## Program: SE

## Curriculum Scheme: Revised 2016

## Examination: Second Year Semester III

## Course Code: ECC402

Course Name: Electronics and devices circuit-II
Time: 1-hour

Max. Marks: 50

Note to the students: - All the Questions are compulsory and carry equal marks.

| Q1. | Identify type of Negative Feedback in following circuit. |
| :---: | :---: |
| Option A: | Voltage series |
| Option B: | Voltage shunt |
| Option C: | Current series |
| Option D: | Current series |
| Q2. | If the output of an amplifier is 10 V and 100 mV from the output is fed back to the input, then feedback fraction is $\qquad$ |
| Option A: | 10 |
| Option B: | 1 |
| Option C: | 15 |
| Option D: | 0.01 |
| Q3. | When negative voltage feedback is applied to an amplifier, its voltage gain ..................? |
| Option A: | increases |
| Option B: | decreases |
| Option C: | No change |
| Option D: | Increases/decreases |
|  |  |
| Q4. | Emitter follower is a .................. circuit. |


| Option A: | Voltage feedback |
| :---: | :---: |
| Option B: | Current feedback |
| Option C: | Both voltage and current feedback |
| Option D: | No feedback |
| Q5. | In class A Power Amplifier power dissipation in transistor under no signal condition is $\qquad$ . |
| Option A: | Less |
| Option B: | More |
| Option C: | Twice the power dissipation under signal condition |
| Option D: | Same as Power dissipation under signal condition |
| Q6. | Heat sink is used in Power transistor to |
| Option A: | Increase Maximum Power dissipation rating of transistor |
| Option B: | Decrease Maximum Power dissipation rating of transistor |
| Option C: | No change in maximum power dissipation rating of transistor |
| Option D: | Increase/Decrease Maximum Power dissipation rating of transistor |
| Q7. | In class $A B$ Power Amplifier in a following figure 1, what is a use of diode. |
| Option A: | Remove cross over distortion |
| Option B: | Provide Temperature compensation |
| Option C: | Improves efficiency |
| Option D: | Improves Voltage gain |
| Q8. | In audio system speaker needs 10Watt of output power, calculate PQmax for |


|  | transistor for Class A and Class B Power Amplifier. Select a suitable Power Amplifier for Audio system. |
| :---: | :---: |
| Option A: | Class A Power Amplifier |
| Option B: | Class B Power Amplifier |
| Option C: | Class A and Cass B Power Amplifier both |
| Option D: | Class A or Class B Power Amplifier |
| Q9. | In class B push pull Power Amplifier deliver 8W of audio power to output load if transformer efficiency 80\%. Calculate Pidc |
| Option A: | 12.73W |
| Option B: | 11.31W |
| Option C: | 13.4W |
| Option D: | 11.13W |
| Q10. | In Class A Power Amplifier output power is $5 \mathrm{~W}, \mathrm{~V}_{\mathrm{CC}}=20 \mathrm{~V}, \mathrm{ICQ}=0.65 \mathrm{~A}$. Determine efficiency of Power Amplifier. |
| Option A: | 46\% |
| Option B: | 38.46\% |
| Option C: | 50\% |
| Option D: | 78.5\% |
| Q11. | Find frequency of wein bridge oscillator $R=1 \mathrm{~K} \Omega, \mathrm{C}=0.1 \mu \mathrm{f}$ |
| Option A: | 1.59 KHz |
| Option B: | 159 KHZ |
| Option C: | 15.9KHZ |
| Option D: | 0.159 KHZ |
| Q12. | Crystal oscillator is used for |
| Option A: | Low frequency, High Q |
| Option B: | High frequency, High Q |
| Option C: | Low frequency, Low Q |
| Option D: | High frequency, Low Q |
| Q13. | While designing an amplifier for TV application, which amplifier will be selected? |
| Option A: | CE- CE Amplifier |


| Option B: | Darlington Pair |
| :--- | :--- |
| Option C: | Cascode Amplifier |
| Option D: | Transformer coupled power amplifier |
|  |  |
| Q14. | For NMOS transistor which of the following is not true? |
| Option A: | The substrate is of p-type semiconductor |
| Option B: | Inversion layer or induced channel is of n type |
| Option C: | Threshold voltage is negative |
| Option D: | Used in VLSI |
|  |  |
| Q15. | For N channel MOSFET IDQ $=1 \mathrm{~mA}, \mathrm{Kn}=0.85 \mathrm{~mA} / \mathrm{V} 2$, VTN $=0.8 \mathrm{~V}$, Find VGS. |
| Option A: | 1.88 V |
| Option B: | 2.3 V |
| Option C: | 0.8 V |
| Option D: | OV |
|  |  |
| Q16. | Select the amplifier for a given specifications <br> Av=100, Ri $=1 \mathrm{MS} \Omega$ |
| Option A: | CS-CS Amplifier |
| Option B: | CS-CE Amplifier |
| Option C: | CE-CE Amplifier |
| Option D: | CE-CS Amplifier |
|  |  |
| Q17. | Configuration used in Cascode Amplifier |
| Option A: | CE-CE |
| Option B: | CE-CB |
| Option C: | CB-CE |
| Option D: | CE-CC |
|  |  |
| Q18. | Select which is not a feature of Darlington |
| Option A: | Combination of CC -CC configuration |
| Option B: | Voltage gain 1 |
| Option C: | Input Resistance Low |
| Option D: | Output resistance High |
|  |  |
| Q19. | Which coupling method introduces HUM in frequency response? |
| Option A: | Direct Coupling |
| Option B: | Transformer Coupling |
| Option C: | RC Coupling |
| Option D: | LC coupling |
|  |  |
| Q20. | In a 2 stage CE - CE amplifier AV1=20, AV2=30.Find total voltage gain. |
| Option A: | 50 |
| Option B: | 600 |
| Option C: | 400 |
|  | 900 |


|  |  |
| :--- | :--- |
| Q21. | In household inverter need to increase number of loads following some <br> suggested modification. <br> 1. Capacity of Battery <br> 2. Increase driving capacity by current gain of an Amplifier <br> 3.Modify Bandwidth of an Amplifier <br> 4. Modify Voltage gain of an Amplifier. <br> select the suitable option |
| Option A: | 3 \& 4 |
| Option B: | 2 \& 3 |
| Option C: | 1 \& 2 |
| Option D: | 3 \& 1 |
| Q22. | While designing an amplifier for TV application, which amplifier will be <br> selected? |
| Option A: | CE- CE Amplifier |
| Option B: | Darlington Pair |
| Option C: | Cascode Amplifier |
| Option D: | CS-CS Amplifier |
|  |  |
| Q23. | In hartly oscillator positive feedback is provided by |
| Option A: | L-C Network |
| Option B: | R-C Network |
| Option C: | Resistive network |
| Option D: | R-C network |
|  |  |
| Q24. | Advancement of technology in a product like mobile phone demands for <br> compactness, less power dissipation, and more efficiency which component <br> satisfies all requirement |
| Option A: | BJT (Bipolar Junction Transistor) |
| Option B: | JFET (Junction Field Effect Transistor) |
| Option C: | MOSFET (Metal Oxide Field Effect Transistor) |
| Option D: | Diode |
|  |  |
| Q25. | In MOSFET, the threshold voltage is the measure of the |
| Option A: | Minimum voltage to form channel |
| Option B: | Minimum voltage to turn of the device |
| Option C: | Maximum voltage to form channel |
| Option D: | Maximum voltage to turn of the device |

